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# PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

## [Abstract]

A process for manufacturing a semiconductor integrated circuit device is disclosed, including the steps of:

- (a) coating a semiconductor substrate with a first conductive film, a first insulating film and a second insulating film and forming a plurality of first conductive film patterns;
- (b) forming a third and fourth insulating films over the second insulating film;
- (c) forming a mask with a first opening over the fourth insulating film, and etching the fourth insulating film to form a second opening in the fourth insulating film;
- (d) anisotropically etching the third insulating film to form a third opening for exposing the upper face of the semiconductor substrate.

Figure 19



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